

ABSTRACT OF THE DISCLOSURE

A nonvolatile semiconductor memory device includes: a semiconductor substrate having a main surface; a pair of p-type impurity diffused regions, formed at the main surface of the semiconductor substrate to serve as source/drain; a floating gate formed on a region of the semiconductor substrate lying between the paired p-type impurity diffused regions, with a tunnel insulating layer interposed between the floating gate and the region of the semiconductor substrate; and an impurity diffused control region formed at the main surface of the semiconductor substrate to control a potential of the floating gate. Accordingly, a nonvolatile semiconductor device can be obtained in which data can be electrically erased and written at a low voltage.